5 light and accumulating the charge for a predetermined
6 period of time;
7 a vertical transfer unit for vertically transferring

8 charge from the pixels in the pixel unit, a horizontal

9 transfer unit for horizontally transferring charge from the 0 vertical transfer unit;

10 vertical transfer unit;

shift gates each provided between each pixel and the vertical transfer unit for reading out the charge in the pixels to the vertical transfer unit, gate electrodes for controlling the shift gates; and

a plurality of lead lines and a plurality of connection terminals for connecting the gate electrodes to an external circuit,

gate control lines connected to gate electrode groups
in which horizontal lines belonging to each coset of modulo
N within successive pixel rows are connected commonly, N
being a predetermined natural number between 4 and one half
the number of pixels in a column, and also being a minimum
number corresponding to a periodic unit of gate electrode
connections to said connection terminals within said
successive pixel rows, being combined with each other so as
to reduce the number of the connection terminals to less

Please replace claim 3 with the following:

- 1 3. (TWICE AMENDED) A solid-state imaging device
- 2 comprising:

than N.

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- a pixel unit constituted by a two-dimensional array of
- 4 pixels for generating charge in correspondence to received
- 5 light and accumulating the charge for a predetermined
- 6 period of time;

7 a vertical transfer unit for vertically transferring charge from the pixels in the pixel unit, a horizontal 8 9 transfer unit for horizontally transferring charge from the 10 vertical transfer unit; 11 shift gates\each provided between each pixel and the 12 vertical transfer unit for reading out the charge in the 13 pixels to the vertical transfer unit, gate electrodes for 14 controlling the shift gates; and 15 a plurality of\lead lines and a plurality of 16 connection terminals for connecting the gate electrodes to 17 an external circuit, 18 the gate electrodes being provided in a predetermined 19 number N of gate electrode groups such that horizontal line 20 number of the gate electrode groups which are connected to 21 respective common lead lines belong to each same residue class of modulo N, N being a predetermined natural number 22 23 between 4 and one half the\number of pixels in a column, 24 and also being a minimum number corresponding to the 25 periodic unit about connections to said connection 26 terminals within said successive pixel rows, some of the

Please replace claim 4 with the following:

1 4. (TWICE AMENDED) A solid-state amaging device

connection terminals are less in number than N.

2 comprising:

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a pixel unit constituted by a two-dimensional array of

gate electrode groups being commonly connected so that the

4 pixels for generating charge in correspondence to received

5 light and accumulating the charge for a predetermined

6 period of time;

a vertical transfer unit for vertically transferring charge from the pixels in the pixel unit, a horizontal transfer unit for horizontally transferring charge from the vertical transfer unit; shift gates each provided between each pixel and the vertical transfer unit for reading out the charge in the pixels to the vertical transfer unit, gate electrodes for controlling the shift gates;

and a plurality of lead lines and a plurality of connection terminals for connecting the gate electrodes to an external circuit,

the gate electrodes making up N of gate electrode groups in which the lines belonging to each coset of modulo N within successive pixel rows are connected to common lead lines, N being a predetermined natural number between 4 and one half the number of pixels in a column, and also being a minimum number corresponding to a periodic unit of gate electrode connections to said connection terminals within said successive pixel rows, the gate electrode groups having common connections to reduce the number of the connection terminals to less than N,

wherein the commonly connected gate electrode groups are always controlled in the same way in each of all predetermined read-out modes including selective pixel read-out modes by selective shift gate driving.

Please replace claim 5 with the following:

- 1 5. (TWICE AMENDED) A solid-state imaging device
- 2 comprising:

a pixel\unit constituted by a two-dimensional array of 3 4 pixels for generating charge in correspondence to received 5 light and accumulating the charge for a predetermined 6 period of time \(\) 7 a vertical\transfer unit for vertically transferring charge from the pixels in the pixel unit, a horizontal 8 9 transfer unit for horizontally transferring charge from the 10 vertical transfer\unit; 11 shift gates each provided between each pixel and the 12 vertical transfer unit for reading out the charge in the 13 pixels to the vertical transfer unit, gate electrodes for 14 controlling the shift gates; and 15 a plurality of lead lines and a plurality of connection terminals for connecting the gate electrodes to 16 17 an external circuit, 18 gate control lines\connected to gate electrode groups in which the horizontal lines belonging to each coset of modulo N within successive pixel rows are connected 21 commonly, N being a predetermined natural number between 4 and one half the number of pixels in a column, and also 22 23 being a minimum number corresponding to a periodic unit of 24 gate electrode connections $t\dot{q}$ said connection terminals 25 within said successive pixel hows, being combined with each 26 other so as to reduce the number of the connection 27 terminals to less than N, 28 wherein the commonly connected gate electrode groups 29 are always controlled in the same way in each of all

Please replace claim 6 with the following:

read-out modes by selective shift gate driving.

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predetermined read-out modes including selective pixel

6. (TWICE AMENDED)\ A solid-state imaging device 1 2 comprising: 3 a pixel unit constituted by a two-dimensional array of 4 pixels for generating charge in correspondence to received light and accumulating the charge for a predetermined 5 6 period of time; a vertical transfer unit for vertically transferring 7 8 charge from the pixels in the pixel unit, a horizontal 9 transfer unit for horizontally transferring charge from the 10 vertical transfer unit; 11 shift gates each provided between each pixel and the 12 vertical transfer unit for\reading out the charge in the pixels to the vertical transfer unit, gate electrodes for controlling the shift gates;\ and a plurality of lead lines and a plurality of connection terminals for connecting the gate electrodes to 17 an external circuit. 18 the gate electrodes being provided in a predetermined 19 number N of gate electrode groups such that horizontal line 20 number of the gate electrode groups which are connected to 21 respective common lead lines belong to each same residue 22 class of modulo N, N being a predetermined natural number 23 between 4 and one half the number of pixels in a column, 24 and also being a minimum number corresponding to the 25 periodic unit about connections to salid connection terminals within successive pixel rows, some of the gate 26 27 electrode groups being commonly connected so that the 28 connection terminals are less in number than N, 29 wherein the commonly connected gate electrode groups 30 are always controlled in the same way in\each of all

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predetermined read-out modes including selective pixel

read-out modes by selective shift gate driving.

Please cancel claim 10 without prejudice to, or disclaimer of, the subject matter recited therein.

Please add the following new claim:

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--11. (NEW) \A solid-state imaging device comprising:

a two-dimensional array of pixels for generating charge in correspondence to received light and accumulating the charge for a predetermined period of time;

a vertical transfer unit for vertically transferring charge from the pixels in the pixel unit;

shift gates each provided between each pixel and the vertical transfer unit for reading out the charge in the pixels to the vertical transfer unit, and a plurality of R gate electrodes for controlling the shift gates; and

a plurality of lead lines and a plurality of connection terminals for connecting the gate electrodes to an external circuit,

wherein the R gate electrodes are divided into S gate groups, each gate group having R/S gate electrodes,

wherein the R gate electrodes are divided into R/S pixel groups, each having R/(R/S) consecutive, adjacent, gate electrodes,

wherein the i^{th} gate electrode of each pixel group, where i = 1 to R/(R/S), share a common connection terminal, and

wherein at least two gate electrodes within a given pixel group share a common connection terminal.--

In accordance with 37 C.F.R. § 1.121(c)(1)(ii), separate sheets with the rewritten claims marked-up to show